

isc Silicon PNP Power Transistor

KTB1367

DESCRIPTION

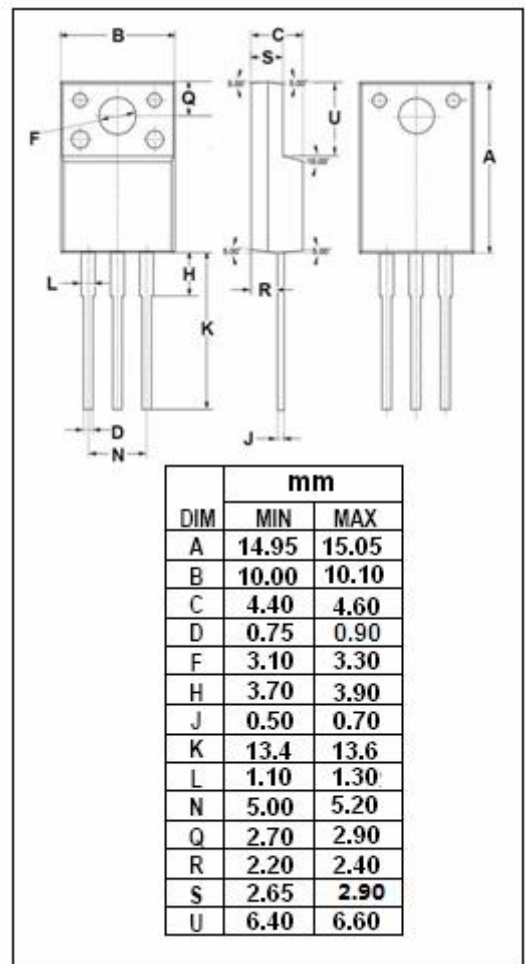
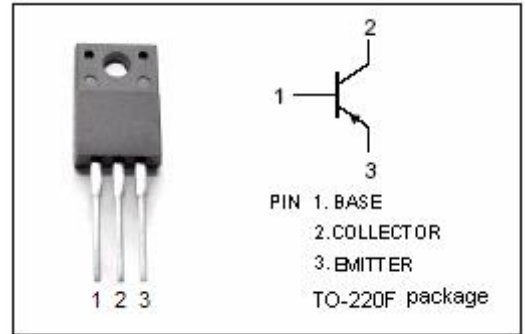
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -100V(\text{Min})$
- Collector Power Dissipation-  
:  $P_C = 30W @ T_C = 25^\circ C$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -2.0V(\text{Max}) @ (I_C = -4A, I_B = -0.4A)$
- Complement to Type KTD2059

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$I_B$	Base Current-Continuous	-0.5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	30	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$



**isc Silicon PNP Power Transistor****KTB1367****ELECTRICAL CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -4A; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	40		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -5V	20			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1MHz		270		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V		5		MHz

◆ **h<sub>FE-1</sub> Classifications**

R	O	Y
40-80	70-140	120-240